

MITSUBISHI IGBT MODULES  
**CM300DU-12NFH**

HIGH POWER SWITCHING USE

**CM300DU-12NFH**



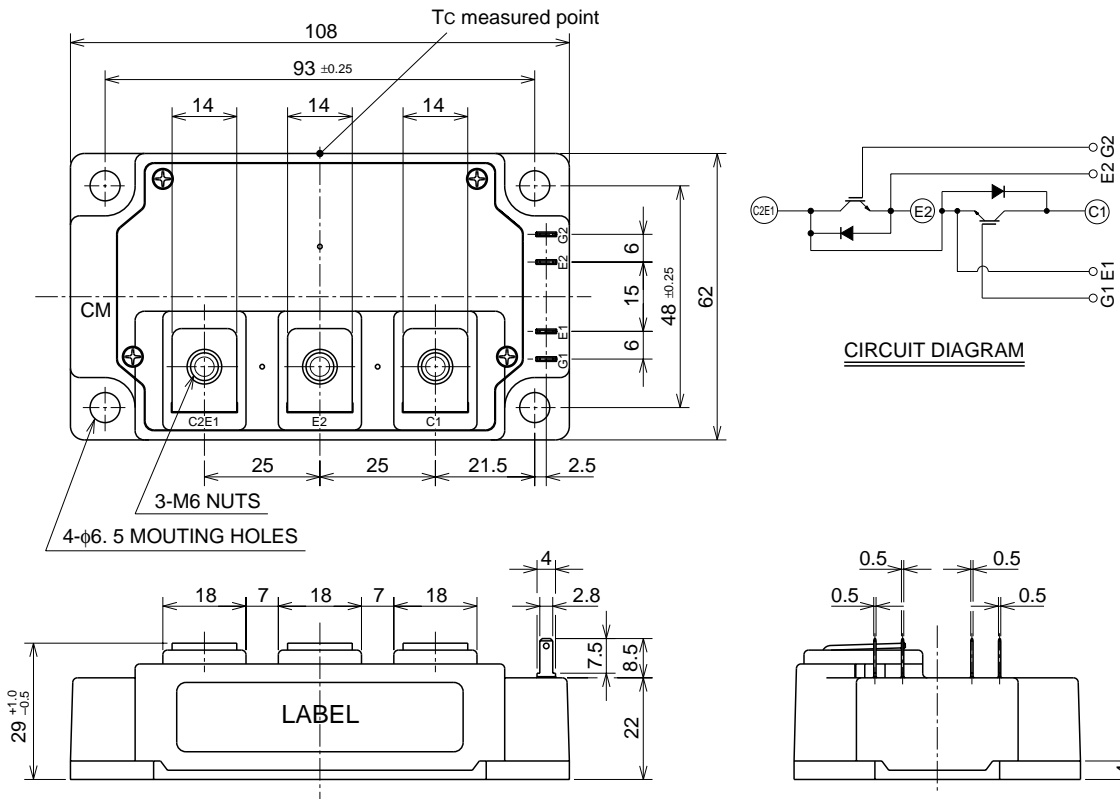
- IC .....300A
- VCES .....600V
- Insulated Type
- 2-elements in a pack

**APPLICATION**

High frequency switching use (30kHz to 60kHz).  
 Gradient amplifier, Induction heating, power supply, etc.

**OUTLINE DRAWING & CIRCUIT DIAGRAM**

Dimensions in mm



## CM300DU-12NFH

## HIGH POWER SWITCHING USE

MAXIMUM RATINGS (T<sub>j</sub> = 25°C)

| Symbol                    | Parameter                     | Conditions                             | Ratings    | Unit  |
|---------------------------|-------------------------------|--|------------|-------|
| V <sub>CE</sub> S         | Collector-emitter voltage     | G-E Short                              | 600        | V     |
| V <sub>GE</sub> S         | Gate-emitter voltage          | C-E Short                              | ±20        | V     |
| I <sub>C</sub>            | Collector current             | Operation                              | 300        | A     |
| I <sub>CM</sub>           |                               | Pulse (Note 2)                         | 600        | A     |
| I <sub>E</sub> (Note 1)   | Emitter current               | Operation                              | 300        | A     |
| I <sub>EM</sub> (Note 1)  |                               | Pulse (Note 2)                         | 600        | A     |
| P <sub>C</sub> (Note 3)   | Maximum collector dissipation | T <sub>C</sub> = 25°C                  | 780        | W     |
| P <sub>C</sub> ' (Note 3) | Maximum collector dissipation | T <sub>C</sub> ' = 25°C <sup>4</sup>   | 1250       | W     |
| T <sub>j</sub>            | Junction temperature          |  | -40 ~ +150 | °C    |
| T <sub>stg</sub>          | Storage temperature           |  | -40 ~ +125 | °C    |
| V <sub>iso</sub>          | Isolation voltage             | Main Terminal to base plate, AC 1 min. | 2500       | V     |
| —                         | Mounting torque               | Main Terminal M6                       | 3.5 ~ 4.5  | N • m |
| —                         |                               | Mounting holes M6                      | 3.5 ~ 4.5  | N • m |
| —                         | Weight                        | Typical value                          | 400        | g     |

ELECTRICAL CHARACTERISTICS (T<sub>j</sub> = 25°C)

| Symbol                   | Parameter                                     | Test conditions  | Limits |      |        | Unit |
|--------------------------|---|--|--------|------|--------|------|
|                          |   |  | Min.   | Typ. | Max.   |      |
| I <sub>CE</sub> S        | Collector cutoff current                      | V <sub>CE</sub> = V <sub>CE</sub> S, V <sub>GE</sub> = 0V  | —      | —    | 1      | mA   |
| V <sub>GE(th)</sub>      | Gate-emitter threshold voltage                | I <sub>C</sub> = 30mA, V <sub>CE</sub> = 10V   | 5      | 6    | 7      | V    |
| I <sub>GE</sub> S        | Gate leakage current                          | V <sub>GE</sub> = V <sub>GE</sub> S, V <sub>CE</sub> = 0V  | —      | —    | 0.5    | μA   |
| V <sub>CE(sat)</sub>     | Collector-emitter saturation voltage (Note 4) | T <sub>j</sub> = 25°C  | —      | 2.0  | 2.7    | V    |
|                          |   | T <sub>j</sub> = 125°C   | —      | 1.95 | —      |      |
| C <sub>ies</sub>         | Input capacitance                             | V <sub>CE</sub> = 10V<br>V <sub>GE</sub> = 0V  | —      | —    | 83     | nF   |
| C <sub>oes</sub>         | Output capacitance                            |  | —      | —    | 5.4    | nF   |
| C <sub>res</sub>         | Reverse transfer capacitance                  |  | —      | —    | 3.0    | nF   |
| Q <sub>G</sub>           | Total gate charge                             | V <sub>CC</sub> = 300V, I <sub>C</sub> = 300A, V <sub>GE</sub> = 15V   | —      | 1860 | —      | nC   |
| t <sub>d(on)</sub>       | Turn-on delay time                            | V <sub>CC</sub> = 300V, I <sub>C</sub> = 300A<br>V <sub>GE1</sub> = V <sub>GE2</sub> = 15V<br>R <sub>G</sub> = 4.2Ω, Inductive load switching operation<br>I <sub>E</sub> = 300A | —      | —    | 350    | ns   |
| t <sub>r</sub>           | Turn-on rise time                             |  | —      | —    | 150    | ns   |
| t <sub>d(off)</sub>      | Turn-off delay time                           |  | —      | —    | 700    | ns   |
| t <sub>f</sub>           | Turn-off fall time                            |  | —      | —    | 150    | ns   |
| t <sub>rr</sub> (Note 1) | Reverse recovery time                         |  | —      | —    | 200    | ns   |
| Q <sub>rr</sub> (Note 1) | Reverse recovery charge                       | —  | 5.5    | —    | μC     |      |
| V <sub>EC</sub> (Note 1) | Emitter-collector voltage                     | I <sub>E</sub> = 300A, V <sub>GE</sub> = 0V  | —      | —    | 2.6    | V    |
| R <sub>th(j-c)Q</sub>    | Thermal resistance*1                          | IGBT part (1/2 module)   | —      | —    | 0.16   | °C/W |
| R <sub>th(j-c)R</sub>    |   | FWDi part (1/2 module)   | —      | —    | 0.24   | °C/W |
| R <sub>th(c-f)</sub>     | Contact thermal resistance                    | Case to fin, Thermal compound Applied*2 (1/2 module)   | —      | 0.04 | —      | °C/W |
| R <sub>th(j-c)Q</sub>    | Thermal resistance                            | T <sub>c</sub> measured point is just under the chips (1/2 module)   | —      | —    | 0.10*3 | °C/W |
| R <sub>G</sub>           | External gate resistance                      |  | 2.1    | —    | 21     | Ω    |

\*1 : T<sub>c</sub> measured point is shown in page OUTLINE DRAWING.

\*2 : Typical value is measured by using Shin-etsu Silicone "G-746".

\*3 : If you use this value, R<sub>th(f-a)</sub> should be measured just under the chips.

\*4 : T<sub>c</sub>' measured point is just under the chips.

Note 1. I<sub>E</sub>, V<sub>EC</sub>, t<sub>rr</sub> & Q<sub>rr</sub> represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWDi).

2. Pulse width and repetition rate should be such that the device junction temp. (T<sub>j</sub>) does not exceed T<sub>jmax</sub> rating.

3. Junction temperature (T<sub>j</sub>) should not increase beyond 150°C.

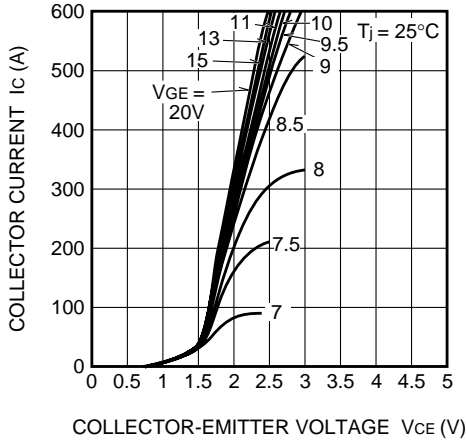
4. No short circuit capability is designed.

# CM300DU-12NFH

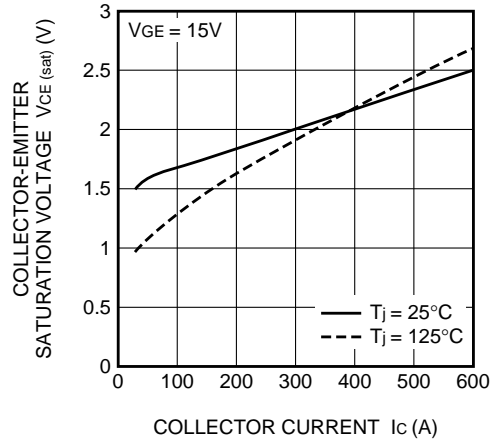
HIGH POWER SWITCHING USE

PERFORMANCE CURVES

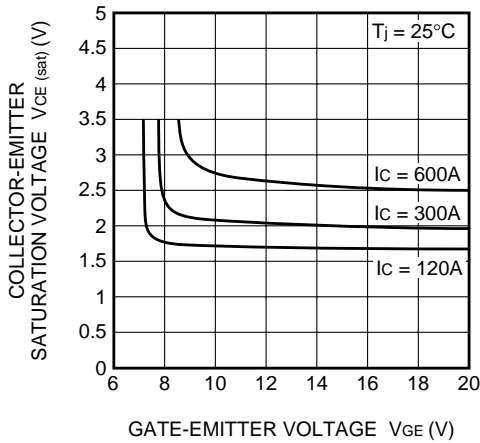
OUTPUT CHARACTERISTICS (TYPICAL)



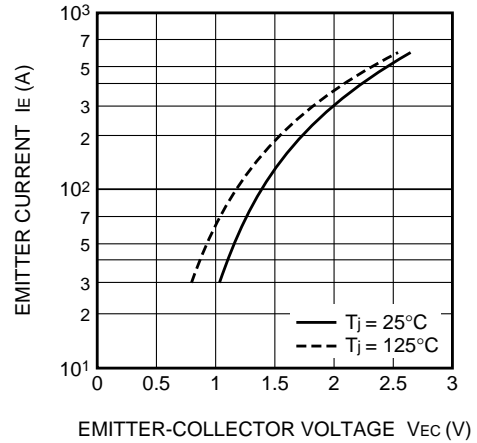
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



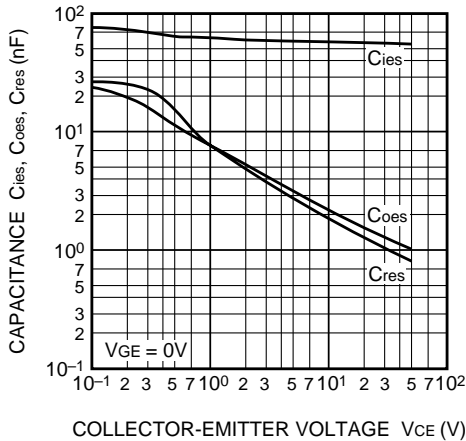
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



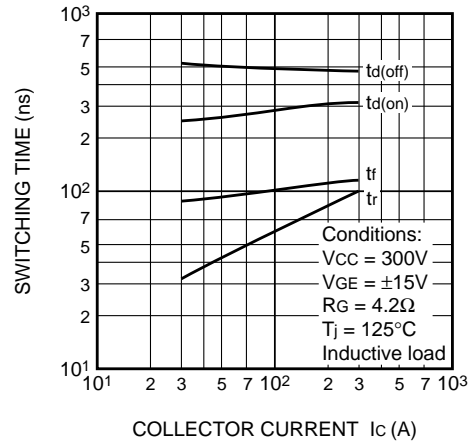
FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



CAPACITANCE- $V_{CE}$  CHARACTERISTICS (TYPICAL)



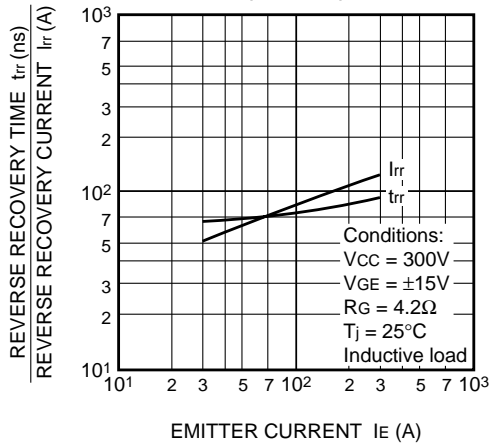
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)



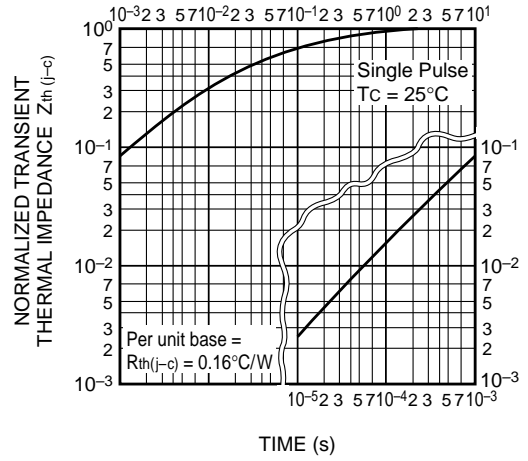
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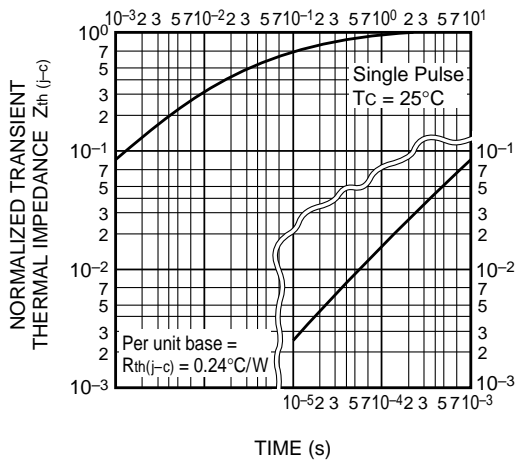
**REVERSE RECOVERY CHARACTERISTICS OF FREE-WHEEL DIODE (TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (IGBT part)**



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (FWDi part)**



**GATE CHARGE CHARACTERISTICS (TYPICAL)**

